

# Mark Hopkinson

## List of Publications by Year in Descending Order

**Source:** <https://exaly.com/author-pdf/6270442/mark-hopkinson-publications-by-year.pdf>

**Version:** 2024-04-24

This document has been generated based on the publications and citations recorded by exaly.com. For the latest version of this publication list, visit the link given above.

The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

512  
papers

9,923  
citations

50  
h-index

78  
g-index

623  
ext. papers

10,877  
ext. citations

3  
avg, IF

5.43  
L-index

#	Paper	IF	Citations
512	Ordered GaAs quantum dots by droplet epitaxy using in situ direct laser interference patterning. <i>Applied Physics Letters</i> , <b>2021</b> , 118, 142101	3.4	2
511	Optical Frequency Comb Generation via Cascaded Intensity and Phase Photonic Crystal Modulators. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , <b>2021</b> , 27, 1-9	3.8	0
510	Broadband enhancement of light-matter interaction in photonic crystal cavities integrating site-controlled quantum dots. <i>Physical Review B</i> , <b>2020</b> , 101,	3.3	10
509	Precise Arrays of Epitaxial Quantum Dots Nucleated by In Situ Laser Interference for Quantum Information Technology Applications. <i>ACS Applied Nano Materials</i> , <b>2020</b> , 3, 4739-4746	5.6	8
508	Formation of laterally ordered quantum dot molecules by in situ nanosecond laser interference. <i>Applied Physics Letters</i> , <b>2020</b> , 116, 201901	3.4	3
507	Broadband, wide-angle antireflection in GaAs through surface nano-structuring for solar cell applications. <i>Scientific Reports</i> , <b>2020</b> , 10, 6269	4.9	5
506	Direct patterning of periodic semiconductor nanostructures using single-pulse nanosecond laser interference. <i>Optics Express</i> , <b>2020</b> , 28, 32529-32539	3.3	5
505	Conditional deletion of E11/Podoplanin in bone protects against ovariectomy-induced increases in osteoclast formation and activity. <i>Bioscience Reports</i> , <b>2020</b> , 40,	4.1	3
504	Photonic integration of uniform GaAs nanowires in hexagonal and honeycomb lattice for broadband optical absorption. <i>AIP Advances</i> , <b>2020</b> , 10, 105211	1.5	0
503	Control of quality factor in laterally coupled vertical cavities. <i>IET Optoelectronics</i> , <b>2020</b> , 14, 100-103	1.5	1
502	Generation of optical frequency combs using a photonic crystal cavity. <i>IET Optoelectronics</i> , <b>2019</b> , 13, 23-26	1.5	1
501	Thermodynamic processes on a semiconductor surface during in-situ multi-beam laser interference patterning. <i>IET Optoelectronics</i> , <b>2019</b> , 13, 7-11	1.5	4
500	Pulse control protocols for preserving coherence in dipolar-coupled nuclear spin baths. <i>Nature Communications</i> , <b>2019</b> , 10, 3157	17.4	8
499	Photonic Crystal Cavity-Based Intensity Modulation for Integrated Optical Frequency Comb Generation. <i>Crystals</i> , <b>2019</b> , 9, 493	2.3	2
498	Site-Controlled Single-Photon Emitters Fabricated by Near-Field Illumination. <i>Advanced Materials</i> , <b>2018</b> , 30, e1705450	24	20
497	Optimisation of the optical emission of bilayers of quantum dots <b>2018</b> , 103-106		
496	Strain relaxation behaviour in In <sub>x</sub> Ga <sub>1-x</sub> As quantum wells on misorientated GaAs (111)B substrates <b>2018</b> , 137-140		

495	Characterization of InGaAs (N)/GaAsN multi-quantum wells using transmission electron microscopy <b>2018</b> , 143-146		
494	Barrier thickness influence on plastic relaxation in (111)B misoriented InGaAs/GaAs double quantum wells <b>2018</b> , 133-136		
493	How InGaAs islands form on GaAs substrates: the missing link in the explanation of the Stranski-Krastanow transition <b>2018</b> , 85-88		
492	Quantum Dots: Site-Controlled Single-Photon Emitters Fabricated by Near-Field Illumination (Adv. Mater. 21/2018). <i>Advanced Materials</i> , <b>2018</b> , 30, 1870147	24	
491	A lithographic approach for quantum dot-photon crystal nanocavity coupling in dilute nitrides. <i>Microelectronic Engineering</i> , <b>2017</b> , 174, 16-19	2.5	9
490	Hypomorphic conditional deletion of E11/Podoplanin reveals a role in osteocyte dendrite elongation. <i>Journal of Cellular Physiology</i> , <b>2017</b> , 232, 3006-3019	7	23
489	Photoluminescence upconversion at GaAs/InGaP2 interfaces driven by a sequential two-photon absorption mechanism. <i>Physical Review B</i> , <b>2016</b> , 93,	3.3	3
488	Few-second-long correlation times in a quantum dot nuclear spin bath probed by frequency-comb nuclear magnetic resonance spectroscopy. <i>Nature Physics</i> , <b>2016</b> , 12, 688-693	16.2	12
487	Endochondral Growth Defect and Deployment of Transient Chondrocyte Behaviors Underlie Osteoarthritis Onset in a Natural Murine Model. <i>Arthritis and Rheumatology</i> , <b>2016</b> , 68, 880-91	9.5	27
486	Suppression of nuclear spin bath fluctuations in self-assembled quantum dots induced by inhomogeneous strain. <i>Nature Communications</i> , <b>2015</b> , 6, 6348	17.4	36
485	Tunable spectral response by hydrogen irradiation of Ga(AsN) superlattice diodes. <i>Applied Physics Letters</i> , <b>2014</b> , 104, 242110	3.4	1
484	How to best measure atomic segregation to grain boundaries by analytical transmission electron microscopy. <i>Journal of Materials Science</i> , <b>2014</b> , 49, 3898-3908	4.3	7
483	III <sub>V</sub> semiconductor devices integrated with silicon. <i>Semiconductor Science and Technology</i> , <b>2013</b> , 28, 090301	1.8	12
482	Element-sensitive measurement of the hole nuclear spin interaction in quantum dots. <i>Nature Physics</i> , <b>2013</b> , 9, 74-78	16.2	61
481	Photonic crystal nanocavities in GaAs/AlGaAs with oxidised bottom cladding. <i>Photonics and Nanostructures - Fundamentals and Applications</i> , <b>2013</b> , 11, 139-144	2.6	9
480	Dual-State Absorber-Photocurrent Characteristics and Bistability of Two-Section Quantum-Dot Lasers. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , <b>2013</b> , 19, 1-9	3.8	8
479	Photoluminescence in Tilted Magnetic Field of Triply Negatively Charged Excitons Hybridized with a Continuum. <i>Acta Physica Polonica A</i> , <b>2013</b> , 124, 798-800	0.6	
478	Dynamic nuclear polarization in InGaAs/GaAs and GaAs/AlGaAs quantum dots under nonresonant ultralow-power optical excitation. <i>Physical Review B</i> , <b>2013</b> , 88,	3.3	12

477	Gain characteristic of dilute nitride HELLSH-VC SOA for 1.3 $\mu\text{m}$ wavelength operation. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2013</b> , 10, 564-566		3
476	Enhancement of activation energies of sharp photoluminescence lines for GaInNAs quantum wells due to quantum confinement. <i>Journal Physics D: Applied Physics</i> , <b>2013</b> , 46, 402001	3	3
475	From the artificial atom to the Kondo-Anderson model: Orientation-dependent magnetophotoluminescence of charged excitons in InAs quantum dots. <i>Physical Review B</i> , <b>2013</b> , 87,	3.3	16
474	Electrical characterisation of p-doped distributed Bragg reflectors in electrically pumped GaInNAs VC SOAs for 1.3 $\mu\text{m}$ operation. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2012</b> , 177, 739-743	3.1	1
473	Structural analysis of strained quantum dots using nuclear magnetic resonance. <i>Nature Nanotechnology</i> , <b>2012</b> , 7, 646-50	28.7	52
472	InAsP-based quantum wells as infrared pressure gauges for use in a diamond anvil cell. <i>Journal of Applied Physics</i> , <b>2012</b> , 112, 074504	2.5	4
471	Impact of the Ga/In ratio on the N incorporation into (In,Ga)(As,N) quantum dots. <i>Journal of Applied Physics</i> , <b>2012</b> , 111, 083530	2.5	
470	Electrical modulation of the optical properties of mid-infrared metamaterials. <i>Applied Physics Letters</i> , <b>2012</b> , 101, 251109	3.4	7
469	Laser location and manipulation of a single quantum tunneling channel in an InAs quantum dot. <i>Physical Review Letters</i> , <b>2012</b> , 108, 117402	7.4	10
468	Polarization-resolved resonant fluorescence of a single semiconductor quantum dot. <i>Applied Physics Letters</i> , <b>2012</b> , 101, 251118	3.4	
467	Polariton states bound to defects in GaAs/AlAs planar microcavities. <i>Physical Review B</i> , <b>2012</b> , 85,	3.3	13
466	In-plane interdot carrier transfer in InAs/GaAs quantum dots. <i>Applied Physics Letters</i> , <b>2012</b> , 100, 152101	3.4	4
465	Catastrophic Optical Damage in Quantum Dot Lasers <b>2012</b> , 93-108		
464	Quantum Dot Switches: Towards Nanoscale Power-Efficient All-Optical Signal Processing <b>2012</b> , 197-221		
463	Thermal quenching of single localized excitons in GaInNAs layers. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 131903	3.4	26
462	In situ control and monitoring of photonic device intermixing during laser irradiation. <i>Optics Express</i> , <b>2011</b> , 19, 9535-40	3.3	1
461	GaInNAs-based Hellsch-vertical cavity semiconductor optical amplifier for 1.3 $\mu\text{m}$ operation. <i>Nanoscale Research Letters</i> , <b>2011</b> , 6, 104	5	14
460	Micro-photoluminescence of GaInNAs layers grown on GaAs substrates of various crystallographic orientations. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2011</b> , 8, 1655-1658		6

459	Charge separation and temperature-induced carrier migration in Ga <sub>1-x</sub> In <sub>x</sub> NyAs <sub>1-y</sub> multiple quantum wells. <i>Physical Review B</i> , <b>2011</b> , 84,	3.3	35
458	Population inversion in a single InGaAs quantum dot using the method of adiabatic rapid passage. <i>Physical Review Letters</i> , <b>2011</b> , 106, 067401	7.4	75
457	Recent progress in short wavelength quantum cascade lasers <b>2011</b> ,		2
456	Observation of phase shifts in a vertical cavity quantum dot switch. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 231101	3.4	18
455	Deep levels in H-irradiated GaAs <sub>1-x</sub> N <sub>x</sub> (x . <i>Journal of Applied Physics</i> , <b>2011</b> , 110, 124508	2.5	8
454	Microcavity quantum-dot systems for non-equilibrium Bose-Einstein condensation. <i>Journal of Physics: Conference Series</i> , <b>2010</b> , 245, 012059	0.3	1
453	Two step optimized process for scanning tunneling microscopy tip fabrication. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , <b>2010</b> , 28, 371-375	1.3	10
452	Cryogenic confocal microscopy with rotation in a magnetic field. <i>Review of Scientific Instruments</i> , <b>2010</b> , 81, 013906	1.7	8
451	Terahertz activated luminescence of trapped carriers in InGaAs/GaAs quantum dots. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 031101	3.4	9
450	Strongly coupled single quantum dot in a photonic crystal waveguide cavity. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 111101	3.4	35
449	Electrical control of fine-structure splitting in self-assembled quantum dots for entangled photon pair creation. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 221108	3.4	19
448	All-optical switch using InAs quantum dots in a vertical cavity <b>2010</b> ,		1
447	State-switched modelocking of two-segment quantum dot laser via self-electro-optical quantum dot absorber. <i>Electronics Letters</i> , <b>2010</b> , 46, 161	1.1	9
446	Reverse-emission-state-transition mode locking of a two-section InAs/InGaAs quantum dot laser. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 071118	3.4	12
445	High performance intermixed p-doped quantum dot superluminescent diodes at 1.2 [micro sign]m. <i>Electronics Letters</i> , <b>2010</b> , 46, 295	1.1	12
444	Reverse ground-state excited-state transition dynamics in two-section quantum dot semiconductor lasers: mode-locking and state-switching <b>2010</b> ,		2
443	Surface band-gap narrowing in quantized electron accumulation layers. <i>Physical Review Letters</i> , <b>2010</b> , 104, 256803	7.4	80
442	Temperature-dependent carrier tunneling for self-assembled InAs/GaAs quantum dots with a GaAsN quantum well injector. <i>Applied Physics Letters</i> , <b>2010</b> , 96, 151104	3.4	22

441	Effects of intermixing on modulation p-doped quantum dot superluminescent light emitting diodes. <i>Optics Express</i> , <b>2010</b> , 18, 7055-63	3.3	21
440	Splitting and lasing of whispering gallery modes in quantum dot micropillars. <i>Optics Express</i> , <b>2010</b> , 18, 22578-92	3.3	16
439	Quantitative investigation of the onset of islanding in strained layer epitaxy of InAs/GaAs by X-ray mapping in STEM. <i>Journal of Physics: Conference Series</i> , <b>2010</b> , 209, 012035	0.3	4
438	Temperature dependence of Ga-assisted oxide desorption on GaAs(001). <i>Journal of Physics: Conference Series</i> , <b>2010</b> , 209, 012066	0.3	3
437	Control of Strain in GaSbAs/InAs/GaAs Quantum Dots. <i>Journal of Physics: Conference Series</i> , <b>2010</b> , 245, 012065	0.3	3
436	InAs/GaAs(001) molecular beam epitaxial growth in a scanning tunnelling microscope. <i>Journal of Physics: Conference Series</i> , <b>2010</b> , 209, 012048	0.3	3
435	Quantum key distribution system in standard telecommunications fiber using a short wavelength single photon source. <i>Journal of Applied Physics</i> , <b>2010</b> , 107, 073102	2.5	12
434	Electroluminescence Studies of Modulation p-Doped Quantum Dot Laser Structures. <i>IEEE Journal of Quantum Electronics</i> , <b>2010</b> , 46, 1847-1853	2	0
433	Detailed Design and Characterization of All-Optical Switches Based on InAs/GaAs Quantum Dots in a Vertical Cavity. <i>IEEE Journal of Quantum Electronics</i> , <b>2010</b> , 46, 1582-1589	2	14
432	Quantum Dot Superluminescent Diodes for Optical Coherence Tomography: Skin Imaging. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , <b>2010</b> , 16, 748-754	3.8	25
431	. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , <b>2010</b> , 16, 1015-1022	3.8	39
430	Theoretical and experimental investigations of the temperature dependent continuous wave lasing characteristics and the switch-on dynamics of an InAs/InGaAs quantum-dot semiconductor laser. <i>Optics Communications</i> , <b>2010</b> , 283, 5092-5098	2	13
429	Voltage-controlled nuclear polarization switching in a single In <sub>x</sub> Ga <sub>1-x</sub> As quantum dot. <i>Physical Review B</i> , <b>2009</b> , 79,	3.3	5
428	Beating of exciton-dressed states in a single semiconductor InGaAs/GaAs quantum dot. <i>Physical Review Letters</i> , <b>2009</b> , 102, 207401	7.4	38
427	Role of segregation in InAs/GaAs quantum dot structures capped with a GaAsSb strain-reduction layer. <i>Physical Review B</i> , <b>2009</b> , 80,	3.3	37
426	Atomic scale high-angle annular dark field STEM analysis of the N configuration in dilute nitrides of GaAs. <i>Physical Review B</i> , <b>2009</b> , 80,	3.3	20
425	Correlation between defect density and current leakage in InAs/GaAs quantum dot-in-well structures. <i>Journal of Applied Physics</i> , <b>2009</b> , 106, 024502	2.5	12
424	Magneto-optical study of thermally annealed InAs-InGaAs-GaAs self-assembled quantum dots. <i>Journal of Applied Physics</i> , <b>2009</b> , 105, 053512	2.5	2

423	DIRECT IMPRINTING OF SiO <sub>2</sub> WAVEGUIDE STRUCTURES ON GaAs AND ITS APPLICATION IN InAs/GaAs QUANTUM DOT INTERMIXING. <i>International Journal of Nanoscience</i> , <b>2009</b> , 08, 107-111	0.6	
422	Tailoring the electrical conductivity of GaAs by nitrogen incorporation. <i>Journal of Physics Condensed Matter</i> , <b>2009</b> , 21, 174209	1.8	4
421	Voltage-controlled motional narrowing in a semiconductor quantum dot. <i>New Journal of Physics</i> , <b>2009</b> , 11, 093032	2.9	2
420	Thermal runaway and optical efficiency in InAs/GaAs quantum dot lasers. <i>Applied Physics Letters</i> , <b>2009</b> , 95, 141106	3.4	5
419	Quantum Well and Dot Self-Aligned Stripe Lasers Utilizing an InGaP Optoelectronic Confinement Layer. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , <b>2009</b> , 15, 819-827	3.8	3
418	Tuning Superluminescent Diode Characteristics for Optical Coherence Tomography Systems by Utilizing a Multicontact Device Incorporating Wavelength-Modulated Quantum Dots. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , <b>2009</b> , 15, 757-763	3.8	20
417	Multi-section quantum dot superluminescent diodes for spectral shape engineering. <i>IET Optoelectronics</i> , <b>2009</b> , 3, 100-104	1.5	11
416	As-rich reconstruction stability observed by high temperature scanning tunnelling microscopy. <i>Journal of Crystal Growth</i> , <b>2009</b> , 311, 4478-4482	1.6	1
415	Dilute (In,Ga)(As,N) thin films grown by molecular beam epitaxy on (100) and non-(100) GaAs substrates: a Raman-scattering study. <i>Journal of Materials Science: Materials in Electronics</i> , <b>2009</b> , 20, 116-119	2.1	5
414	Limits of In(Ga)As/GaAs quantum dot growth. <i>Physica Status Solidi (B): Basic Research</i> , <b>2009</b> , 246, 717-720.	0.3	7
413	Two-colour photocurrent detection technique for coherent control of a single InGaAs/GaAs quantum dot. <i>Physica Status Solidi (B): Basic Research</i> , <b>2009</b> , 246, 824-827	1.3	1
412	Dependence of N incorporation into (Ga)InAsN QDs on Ga content probed by rapid thermal annealing. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2009</b> , 6, 1441-1444		5
411	Electrical properties of nitrogen-related defects in n-type GaAsN grown by molecular-beam epitaxy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2009</b> , 6, 2652-2654		11
410	Maximising performance of optical coherence tomography systems using a multi-section chirped quantum dot superluminescent diode. <i>Microelectronics Journal</i> , <b>2009</b> , 40, 588-591	1.8	11
409	Towards coherent optical control of a single hole spin: Rabi rotation of a trion conditional on the spin state of the hole. <i>Solid State Communications</i> , <b>2009</b> , 149, 1458-1465	1.6	2
408	GaAs(001) (2 $\times$ 2) to c(4 $\times$ 4) transformation observed in situ by STM during As flux irradiation. <i>Surface Science</i> , <b>2009</b> , 603, 2398-2402	1.8	3
407	InAs/GaAs(001) wetting layer formation observed in situ by concurrent MBE and STM. <i>Surface Science</i> , <b>2009</b> , 603, 3439-3444	1.8	6
406	Empirical bond order potential calculations of the elastic properties of epitaxial InGaSbAs layers. <i>Microelectronics Journal</i> , <b>2009</b> , 40, 533-536	1.8	1

405	Electric field effects on the carrier migration in self-assembled InAs/GaAs quantum dots. <i>Microelectronics Journal</i> , <b>2009</b> , 40, 838-840	1.8	3
404	InAs/GaAs quantum dots morphology: Nanometric scale HAADF simulations. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2009</b> , 165, 88-93	3.1	2
403	Coherence function control of Quantum Dot Superluminescent Light Emitting Diodes by frequency selective optical feedback. <i>Optics Express</i> , <b>2009</b> , 17, 13365-72	3.3	6
402	3.1 $\mu\text{m}$ room temperature InGaAs/AlAsSb/InP quantum cascade lasers. <i>Applied Physics Letters</i> , <b>2009</b> , 94, 031106	3.4	45
401	Enhanced room-temperature quantum-dot effects in modulation-doped InAs/GaAs quantum dots. <i>Applied Physics Letters</i> , <b>2009</b> , 95, 171902	3.4	13
400	Vertical-geometry all-optical switches based on InAs/GaAs quantum dots in a cavity. <i>Applied Physics Letters</i> , <b>2009</b> , 95, 021109	3.4	31
399	Dependence of the Electroluminescence on the Spacer Layer Growth Temperature of Multilayer Quantum-Dot Laser Structures. <i>IEEE Journal of Quantum Electronics</i> , <b>2009</b> , 45, 79-85	2	8
398	Fine Structure of the Localized Emission from GaInNAs Layers Studied by Micro-Photoluminescence. <i>Acta Physica Polonica A</i> , <b>2009</b> , 116, 930-932	0.6	1
397	Room Temperature InGaAs-AlAsSb Quantum Cascade Lasers Operating in 3 $\mu\text{m}$ Range <b>2009</b> ,		1
396	Origin of Temperature-Dependent Threshold Current in p-Doped and Undoped In(Ga)As Quantum Dot Lasers. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , <b>2008</b> , 14, 1162-1170	3.8	15
395	Low-Threshold 1.3- $\mu\text{m}$ GaInNAs Quantum-Well Lasers Using Quaternary-Barrier Structures. <i>IEEE Photonics Technology Letters</i> , <b>2008</b> , 20, 942-944	2.2	2
394	Two photon absorption in quantum dot-in-a-well infrared photodetectors. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 023501	3.4	16
393	Quantum dot dipole orientation and excitation efficiency of micropillar modes. <i>Optics Express</i> , <b>2008</b> , 16, 19201-7	3.3	4
392	Simple theoretical model for the temperature stability of InAs/GaAs self-assembled quantum dot lasers with different p-type modulation doping levels. <i>Applied Physics Letters</i> , <b>2008</b> , 93, 161103	3.4	8
391	High power, broad spectral width, 1300nm quantum-dot superluminescent diodes <b>2008</b> ,		2
390	A Quantum Dot Swept Laser Source Based upon a Multisection Laser Device. <i>Japanese Journal of Applied Physics</i> , <b>2008</b> , 47, 2965-2967	1.4	1
389	Long nuclear spin polarization decay times controlled by optical pumping in individual quantum dots. <i>Physical Review B</i> , <b>2008</b> , 77,	3.3	23
388	Two-qubit conditional quantum-logic operation in a single self-assembled quantum dot. <i>Physical Review B</i> , <b>2008</b> , 78,	3.3	49



387	Intersublevel polaron dephasing in self-assembled quantum dots. <i>Physical Review B</i> , <b>2008</b> , 77,	3.3	19
386	Electron coherence length and mobility in highly mismatched III-N-V alloys. <i>Applied Physics Letters</i> , <b>2008</b> , 93, 252106	3.4	16
385	Enhanced nonradiative Auger recombination in p-type modulation doped InAs/GaAs quantum dots. <i>Applied Physics Letters</i> , <b>2008</b> , 93, 101903	3.4	17
384	Selective disordering of InAs/InGaAs dots-in-a-well structure patterned with sol-gel derived SiO <sub>2</sub> strips imprinted by soft mold technique. <i>Applied Physics Letters</i> , <b>2008</b> , 93, 071907	3.4	2
383	Carrier lifetimes in type-II InAs quantum dots capped with a GaAsSb strain reducing layer. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 251905	3.4	37
382	Anomalous photocurrent in self-assembled InAs/GaAs quantum dots. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 182102	3.4	3
381	Nuclear spin pumping under resonant optical excitation in a quantum dot. <i>Applied Physics Letters</i> , <b>2008</b> , 93, 073113	3.4	13
380	High field electron dynamics in dilute nitride Ga(AsN). <i>Applied Physics Letters</i> , <b>2008</b> , 93, 022111	3.4	5
379	Structural analysis of life tested 1.3 fh quantum dot lasers. <i>Journal of Applied Physics</i> , <b>2008</b> , 103, 014913	2.5	40
378	Structural properties of GaAsN/GaAs quantum wells studied at the atomic scale by cross-sectional scanning tunneling microscopy. <i>Applied Physics Letters</i> , <b>2008</b> , 93, 083103	3.4	16
377	Electron effective mass and Si-donor binding energy in GaAs <sub>1-x</sub> N <sub>x</sub> probed by a high magnetic field. <i>Physical Review B</i> , <b>2008</b> , 77,	3.3	10
376	Fast optical preparation, control, and readout of a single quantum dot spin. <i>Physical Review Letters</i> , <b>2008</b> , 100, 197401	7.4	120
375	High Resolution HAADF-STEM Imaging Analysis of N related defects in GaNAs Quantum Wells. <i>Microscopy and Microanalysis</i> , <b>2008</b> , 14, 318-319	0.5	4
374	High-performance 1300-nm InAs/GaAs quantum-dot lasers <b>2008</b> ,		5
373	The evolution of Ga and As core levels in the formation of Fe/GaAs (001): A high resolution soft x-ray photoelectron spectroscopic study. <i>Journal of Applied Physics</i> , <b>2008</b> , 104, 024516	2.5	8
372	The use of Abell-Mersoff potentials in atomistic simulations of InGaAsSb/GaAs. <i>Optical and Quantum Electronics</i> , <b>2008</b> , 40, 1143-1148	2.4	1
371	GaNAs(Sb) surface normal devices. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2008</b> , 205, 85-92	1.6	7
370	Structure of InAs quantum dots-in-a-well nanostructures. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2008</b> , 40, 1988-1990	3	7

- 369 Influence of the Growth Temperature on the Composition Fluctuations of GaInNAs/GaAs Quantum Wells **2008**, 199-221
- 368 Growth and in vivo STM of III-V Compound Semiconductors. *Springer Proceedings in Physics*, **2008**, 471-476.2 6
- 367 Investigating the Capping of InAs Quantum Dots by InGaAs. *Springer Proceedings in Physics*, **2008**, 259-262.2 3
- 366 Comparing InGaAs and GaAsSb Metamorphic Buffer Layers on GaAs Substrates for InAs Quantum Dots Emitting at 1.55 $\mu$ m. *Springer Proceedings in Physics*, **2008**, 263-268 0.2 2
- 365 InGaAs/AlAsSb/InP quantum cascade lasers operating at wavelengths close to 3 $\mu$ m. *Applied Physics Letters*, **2007**, 90, 021108 3-4 74
- 364 Optical transitions in type-II InAs/GaAs quantum dots covered by a GaAsSb strain-reducing layer. *Applied Physics Letters*, **2007**, 91, 021102 3-4 62
- 363 High performance 2.2  $\mu$ m optically-pumped vertical external-cavity surface-emitting laser. *Journal of Modern Optics*, **2007**, 54, 1677-1683 1.1 4
- 362 Double transit region Gunn diodes. *Semiconductor Science and Technology*, **2007**, 22, 245-248 1.8 4
- 361 High-Power and Broadband Quantum Dot Superluminescent Diodes Centered at 1250 nm for Optical Coherence Tomography. *IEEE Journal of Selected Topics in Quantum Electronics*, **2007**, 13, 1267-1272 3.8 12
- 360 Mode structure of the L3 photonic crystal cavity. *Applied Physics Letters*, **2007**, 90, 241117 3-4 85
- 359 High-Power 1.3- $\mu$ m Quantum-Dot Superluminescent Light-Emitting Diode Grown by Molecular Beam Epitaxy. *IEEE Photonics Technology Letters*, **2007**, 19, 109-111 2.2 7
- 358 Intensity noise of ultrabroadband quantum dot light emitting diodes and lasers at 1.3  $\mu$ m **2007**, 4
- 357 Temperature-Dependent Gain and Threshold in P-Doped Quantum Dot Lasers. *IEEE Journal of Selected Topics in Quantum Electronics*, **2007**, 13, 1261-1266 3.8 26
- 356 Single photon sources based upon single quantum dots in semiconductor microcavity pillars. *Journal of Modern Optics*, **2007**, 54, 453-465 1.1 15
- 355 Optical phonon behavior in strain-free dilute Ga(As,N) studied by Raman scattering. *Journal of Applied Physics*, **2007**, 102, 013502 2.5 9
- 354 Spectroscopic evaluation of the structural and compositional properties of GaN<sub>x</sub>As<sub>1-x</sub> superlattices grown by molecular beam epitaxy. *Thin Solid Films*, **2007**, 515, 4430-4434 2.2 2
- 353 Optical characterization of (In,Ga)(As,N) thin films grown by molecular beam epitaxy on non-(1 0 0) GaAs substrates. *Journal of Crystal Growth*, **2007**, 301-302, 552-555 1.6 1
- 352 Kinetic considerations on the phase separation of GaInNAs quantum wells. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2007**, 4, 1477-1480

351	Electric field effect in the spin dynamics of self-assembled InAs/GaAs quantum dots. <i>Journal of Magnetism and Magnetic Materials</i> , <b>2007</b> , 316, e52-e55	2.8	
350	Avalanche Multiplication in InAlAs. <i>IEEE Transactions on Electron Devices</i> , <b>2007</b> , 54, 11-16	2.9	57
349	Effect of Dead Space on Low-Field Avalanche Multiplication in InP. <i>IEEE Transactions on Electron Devices</i> , <b>2007</b> , 54, 2051-2054	2.9	6
348	Dynamics of carriers photogenerated in a dot-in-a-well nanostructure. <i>Laser Physics</i> , <b>2007</b> , 17, 305-309	1.2	3
347	Coherent control of single quantum dot exciton embedded in a photodiode. <i>Journal of Modern Optics</i> , <b>2007</b> , 54, 1717-1722	1.1	
346	GROWTH AND CHARACTERIZATION OF MULTI-LAYER 1.3 $\mu\text{m}$ QUANTUM DOT LASERS. <i>International Journal of Nanoscience</i> , <b>2007</b> , 06, 291-296	0.6	1
345	PROBING THE SCATTERING POTENTIAL OF N-IMPURITIES IN GaAs BY MAGNETO-TUNNELING. <i>International Journal of Modern Physics B</i> , <b>2007</b> , 21, 1600-1604	1.1	
344	Reduced temperature sensitivity of lasing wavelength in near-1.3 $\mu\text{m}$ InAs/GaAs quantum-dot laser with stepped composition strain-reducing layer. <i>Electronics Letters</i> , <b>2007</b> , 43, 670	1.1	5
343	Broadband quantum dot superluminescent LED with angled facet formed by focused ion beam etching. <i>Electronics Letters</i> , <b>2007</b> , 43, 587	1.1	3
342	Fabrication of InAs photodiodes with reduced surface leakage current <b>2007</b> , 6740, 51		12
341	Focused ion beam etching for the fabrication of micropillar microcavities made of III-V semiconductor materials. <i>Journal of Vacuum Science &amp; Technology B</i> , <b>2007</b> , 25, 1197		6
340	Gain in p-doped quantum dot lasers. <i>Journal of Applied Physics</i> , <b>2007</b> , 101, 013107	2.5	24
339	Singlet and triplet polaron relaxation in doubly charged self-assembled quantum dots. <i>New Journal of Physics</i> , <b>2007</b> , 9, 259-259	2.9	10
338	Stark shift of the spectral response in quantum dots-in-a-well infrared photodetectors. <i>Journal of Physics D: Applied Physics</i> , <b>2007</b> , 40, 5537-5540	3	20
337	Low threshold current density and negative characteristic temperature 1.3 $\mu\text{m}$ InAs self-assembled quantum dot lasers. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 111102	3.4	39
336	High Q modes in elliptical microcavity pillars. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 161105	3.4	22
335	Control of polarization and mode mapping of small volume high Q micropillars. <i>Journal of Applied Physics</i> , <b>2007</b> , 102, 043105	2.5	12
334	All-optical switching in quantum cascade lasers. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 053505	3.4	16

333	Coherent response of a quantum dot exciton driven by a rectangular spectrum optical pulse. <i>Physical Review B</i> , <b>2007</b> , 75,	3-3	15
332	Tuning the photoresponse of quantum dot infrared photodetectors across the 8–12 $\mu\text{m}$ atmospheric window via rapid thermal annealing. <i>Applied Physics Letters</i> , <b>2007</b> , 91, 143502	3-4	18
331	Suppression of InAs/GaAs quantum dot decomposition by the incorporation of a GaAsSb capping layer. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 213105	3-4	75
330	Long wavelength bulk GaInNAs p-i-n photodiodes lattice matched to GaAs. <i>Journal of Applied Physics</i> , <b>2007</b> , 101, 064506	2-5	18
329	Effects of photon and thermal coupling mechanisms on the characteristics of self-assembled InAs/GaAs quantum dot lasers. <i>Physical Review B</i> , <b>2007</b> , 76,	3-3	12
328	Effect of facet angle on effective facet reflectivity and operating characteristics of quantum dot edge emitting lasers and superluminescent light-emitting diodes. <i>Applied Physics Letters</i> , <b>2007</b> , 91, 081112	3-4	19
327	Nuclear spin switch in semiconductor quantum dots. <i>Physical Review Letters</i> , <b>2007</b> , 98, 026806	7-4	117
326	All semiconductor swept laser source utilizing quantum dots. <i>Applied Physics Letters</i> , <b>2007</b> , 91, 121119	3-4	10
325	Magnetophonon oscillations in the negative differential conductance of dilute nitride GaAs <sub>1-x</sub> N <sub>x</sub> submicron diodes. <i>Physical Review B</i> , <b>2007</b> , 75,	3-3	11
324	Photoluminescence of InNAs alloys: S-shaped temperature dependence and conduction-band nonparabolicity. <i>Physical Review B</i> , <b>2007</b> , 76,	3-3	29
323	Whispering gallery resonances in semiconductor micropillars. <i>Applied Physics Letters</i> , <b>2007</b> , 91, 071115	3-4	31
322	Molecular Beam Epitaxial Growth of High Power Quantum Dot Super-Luminescent Diodes. <i>Japanese Journal of Applied Physics</i> , <b>2007</b> , 46, 2418-2420	1-4	6
321	Zero and Controllable Linewidth Enhancement Factor in p-Doped 1.3 $\mu\text{m}$ Quantum Dot Lasers. <i>Japanese Journal of Applied Physics</i> , <b>2007</b> , 46, 2421-2423	1-4	9
320	Mapping of the Initial Volume at the Onset of Plasticity in Nanoindentation. <i>Materials Research Society Symposia Proceedings</i> , <b>2007</b> , 1049, 1		
319	Maximising the gain: optimising the carrier distribution in InGaAs quantum dot lasers <b>2007</b> ,		1
318	Room-temperature broadband emission of an InGaAs/GaAs quantum dots laser. <i>Optics Letters</i> , <b>2007</b> , 32, 44-6	3	57
317	Polarized quantum dot emission from photonic crystal nanocavities studied under moderate resonant enhanced excitation. <i>Optics Express</i> , <b>2007</b> , 15, 17221-30	3-3	36
316	Excess Avalanche Noise in $\text{In}_{0.52}\text{Al}_{0.48}\text{As}$ . <i>IEEE Journal of Quantum Electronics</i> , <b>2007</b> , 43, 503-507	2	50

315	Nonradiative Recombination in Multiple Layer In(Ga)As Quantum-Dot Lasers. <i>IEEE Journal of Quantum Electronics</i> , <b>2007</b> , 43, 698-703	2	6
314	. <i>IEEE Journal of Quantum Electronics</i> , <b>2007</b> , 43, 1129-1139	2	56
313	InGaAs/AlAsSb/InP strain compensated quantum cascade lasers. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 151105	3-4	15
312	Improved performance of In <sub>0.6</sub> Ga <sub>0.4</sub> As/AlAs <sub>0.67</sub> Sb <sub>0.33</sub> InP quantum cascade lasers by introduction of AlAs barriers in the active regions. <i>Applied Physics Letters</i> , <b>2007</b> , 91, 051123	3-4	14
311	Atomic scale study of the impact of the strain and composition of the capping layer on the formation of InAs quantum dots. <i>Journal of Applied Physics</i> , <b>2007</b> , 101, 081707	2-5	43
310	Energy level structure and electron relaxation times in InAs/InGaAs quantum dot-in-a-well structures. <i>Applied Physics Letters</i> , <b>2007</b> , 91, 253502	3-4	33
309	Effects of alloy intermixing on the lateral confinement potential in InAs/GaAs self-assembled quantum dots probed by intersublevel absorption spectroscopy. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 163107	3-4	16
308	Magnetic field tuning of hot electron resonant capture in a semiconductor device. <i>Applied Physics Letters</i> , <b>2007</b> , 91, 142104	3-4	4
307	Measurement of modal absorption, gain and recombination in p-doped and intrinsic quantum dot structures. <i>IEE Proceedings: Optoelectronics</i> , <b>2006</b> , 153, 316-320		11
306	Broad-Band Superluminescent Light Emitting Diodes Incorporating Quantum Dots in Compositionally Modulated Quantum Wells. <i>Japanese Journal of Applied Physics</i> , <b>2006</b> , 45, 2542-2545	1-4	13
305	Nitrogen incorporation into strained (In, Ga) (As, N) thin films grown on (100), (511), (411), (311), and (111) GaAs substrates studied by photoreflectance spectroscopy and high-resolution x-ray diffraction. <i>Journal of Applied Physics</i> , <b>2006</b> , 100, 093522	2-5	30
304	1.3 [micro sign]m InAs/GaAs quantum-dot laser with low-threshold current density and negative characteristic temperature above room temperature. <i>Electronics Letters</i> , <b>2006</b> , 42, 922	1-1	28
303	1.34 [micro sign]m GaInNAs quantum well lasers with low room-temperature threshold current density. <i>Electronics Letters</i> , <b>2006</b> , 42, 923	1-1	12
302	High performance 1.3[μm] InAs/GaAs quantum dot lasers with low threshold current and negative characteristic temperature <b>2006</b> , 6184, 374		6
301	High-performance 1.3 μm InAs/GaAs quantum-dot lasers with low threshold current and negative characteristic temperature. <i>IEE Proceedings: Optoelectronics</i> , <b>2006</b> , 153, 280-283		4
300	Temperature dependence of threshold current in p-doped quantum dot lasers. <i>Applied Physics Letters</i> , <b>2006</b> , 89, 151118	3-4	31
299	Effects of growth temperature on the structural and optical properties of 1.6[μm] GaInNAs/GaAs multiple quantum wells. <i>Applied Physics Letters</i> , <b>2006</b> , 88, 191907	3-4	15
298	Strong effect of resonant impurities on Landau-level quantization. <i>Physical Review Letters</i> , <b>2006</b> , 96, 236802	7-4	8

297	Broadband 6th. <i>Applied Physics Letters</i> , <b>2006</b> , 88, 121109	3-4	17
296	Investigation of carrier dynamics on InAs quantum dots embedded in InGaAs/AlAs quantum wells based on time-resolved pump and probe differential photoluminescence. <i>Applied Physics Letters</i> , <b>2006</b> , 89, 181924	3-4	24
295	Role of elastic anisotropy in the vertical alignment of In(Ga)As quantum dot superlattices. <i>Applied Physics Letters</i> , <b>2006</b> , 88, 193118	3-4	17
294	Modifying the electronic properties of GaAs/AlAs superlattices with low-density nitrogen doping. <i>Journal of Applied Physics</i> , <b>2006</b> , 100, 063718	2-5	7
293	Infrared modulated interlevel spectroscopy of 1.3th self-assembled quantum dot lasers using a free electron laser. <i>Applied Physics Letters</i> , <b>2006</b> , 88, 081108	3-4	8
292	Intraband magnetospectroscopy of singly and doubly charged n-type self-assembled quantum dots. <i>Physical Review B</i> , <b>2006</b> , 74,	3-3	25
291	Intra-valence band transitions in self-assembled InAs/AlAs quantum dots studied using photocurrent spectroscopy. <i>Journal of Applied Physics</i> , <b>2006</b> , 100, 013106	2-5	9
290	Control of polarized single quantum dot emission in high-quality-factor microcavity pillars. <i>Applied Physics Letters</i> , <b>2006</b> , 88, 051113	3-4	33
289	Coherent near-infrared wavelength conversion in semiconductor quantum cascade lasers. <i>Applied Physics Letters</i> , <b>2006</b> , 89, 183507	3-4	7
288	p-doped 1.3th InAs/AlAs quantum-dot laser with a low threshold current density and high differential efficiency. <i>Applied Physics Letters</i> , <b>2006</b> , 89, 073113	3-4	72
287	Electric field induced blueshift of the e1-hh1 exciton transition in a GaAs1-xNx/AlAs (x. <i>Applied Physics Letters</i> , <b>2006</b> , 89, 261110	3-4	2
286	Design, growth, fabrication, and characterization of InAs/AlAs 1.3th quantum dot broadband superluminescent light emitting diode. <i>Journal of Applied Physics</i> , <b>2006</b> , 100, 103105	2-5	16
285	Exciton fine structure splitting in dot-in-a-well structures. <i>Applied Physics Letters</i> , <b>2006</b> , 88, 131115	3-4	5
284	Observation and Modeling of a Room-Temperature Negative Characteristic Temperature 1.3- $\mu\text{m}$ p-Type Modulation-Doped Quantum-Dot Laser. <i>IEEE Journal of Quantum Electronics</i> , <b>2006</b> , 42, 1259-1265	2	33
283	Broad-band superluminescent light-emitting diodes incorporating quantum dots in compositionally modulated quantum wells. <i>IEEE Photonics Technology Letters</i> , <b>2006</b> , 18, 58-60	2-2	49
282	. <i>IEEE Photonics Technology Letters</i> , <b>2006</b> , 18, 965-967	2-2	15
281	Integration of a resonant tunneling diode and an optical communications laser. <i>IEEE Photonics Technology Letters</i> , <b>2006</b> , 18, 1518-1520	2-2	5
280	Improved performance of 1.3-th In(Ga)As quantum-dot lasers by modifying the temperature profile of the GaAs spacer layers. <i>IEEE Photonics Technology Letters</i> , <b>2006</b> , 18, 1557-1559	2-2	8

279	High Power, Very Low Noise, C.W. Operation of 1.32 $\mu$ m Quantum-Dot Fabry-Perot Laser Diodes <b>2006,</b>		2
278	The effect of p doping in InAs quantum dot lasers. <i>Applied Physics Letters</i> , <b>2006</b> , 88, 111113	3-4	35
277	Broad-band superluminescent light emitting diodes incorporating quantum dots in compositionally modulated quantum wells <b>2006,</b>		1
276	High power and very low noise operation at 1.3 and 1.5 $\mu$ m with quantum dot and quantum dash Fabry-Perot lasers for microwave links <b>2006</b> , 6399, 158		3
275	Effect of the Growth Temperature in the Composition Fluctuation of GaInNAs/GaAs Quantum Wells. <i>Microscopy and Microanalysis</i> , <b>2006</b> , 12, 754-755	0.5	
274	The control of size and areal density of InAs self-assembled quantum dots in selective area molecular beam epitaxy on GaAs (0 0 1) surface. <i>Microelectronics Journal</i> , <b>2006</b> , 37, 1505-1510	1.8	2
273	RF-plasma source qualification and compositional characterisation of GaNAs superlattices using SIMS. <i>Applied Surface Science</i> , <b>2006</b> , 252, 7218-7220	6.7	6
272	Polarisation control and emission enhancement of a quantum dot in ultra-high finesse microcavity pillars. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2006</b> , 32, 500-503	3	4
271	Effect of GaAs polycrystal on the size and areal density of InAs quantum dots in selective area molecular beam epitaxy. <i>Journal of Crystal Growth</i> , <b>2006</b> , 297, 38-43	1.6	3
270	Photoluminescence beyond 1.5 $\mu$ m from InAs quantum dots. <i>Microelectronics Journal</i> , <b>2006</b> , 37, 1468-1470	1.8	7
269	Optical study of resonant states in GaN x As $_{1-x}$ . <i>Semiconductors</i> , <b>2006</b> , 40, 1162-1164	0.7	
268	Mid-Infrared Optical Coherence Tomography: Application in Tissue Engineering <b>2006,</b>		1
267	Dynamics of the wetting-Layer-quantum-dot interaction in InGaAs self-assembled systems. <i>IEEE Journal of Quantum Electronics</i> , <b>2005</b> , 41, 344-350	2	11
266	The Mechanism of the Stranski-Krastanov Transition <b>2005</b> , 71-88		
265	Mechanism for improvements of optical properties of 1.3- $\mu$ m InAs/GaAs quantum dots by a combined InAlAs/InGaAs cap layer. <i>Journal of Applied Physics</i> , <b>2005</b> , 98, 083516	2.5	20
264	Integration of a resonant tunneling diode and an optical communications laser <b>2005,</b>		1
263	Observation of ultrahigh quality factor in a semiconductor microcavity. <i>Applied Physics Letters</i> , <b>2005</b> , 86, 191109	3-4	27
262	High-performance three-layer 1.3- $\mu$ m InAs-GaAs quantum-dot lasers with very low continuous-wave room-temperature threshold currents. <i>IEEE Photonics Technology Letters</i> , <b>2005</b> , 17, 1139-1141	2.2	101

261	Improved temperature performance of 1.31- $\mu\text{m}$ quantum dot lasers by optimized ridge waveguide design. <i>IEEE Photonics Technology Letters</i> , <b>2005</b> , 17, 1785-1787	2.2	6
260	The role of high growth temperature GaAs spacer layers in 1.3- $\mu\text{m}$ In(Ga)As quantum-dot lasers. <i>IEEE Photonics Technology Letters</i> , <b>2005</b> , 17, 2011-2013	2.2	16
259	An approach to the formation mechanism of the composition fluctuation in GaInNAs quantum wells. <i>Semiconductor Science and Technology</i> , <b>2005</b> , 20, 1096-1102	1.8	5
258	Unfaulting of dislocation loops in the GaInNAs alloy: An estimation of the stacking fault energy. <i>Journal of Applied Physics</i> , <b>2005</b> , 98, 023521	2.5	5
257	Time-resolved photoluminescence measurements of InAs self-assembled quantum dots (Invited Paper) <b>2005</b> ,		3
256	Growth and characterization of multiple layer quantum dot lasers <b>2005</b> ,		1
255	Effect of the growth parameters on the structure and morphology of InAs/InGaAs/GaAs DWELL quantum dot structures. <i>Journal of Crystal Growth</i> , <b>2005</b> , 278, 151-155	1.6	10
254	Structural studies of a combined InAlAs/InGaAs capping layer on 1.3- $\mu\text{m}$ InAs/GaAs quantum dots. <i>Journal of Crystal Growth</i> , <b>2005</b> , 285, 17-23	1.6	17
253	Lasing and spontaneous emission characteristics of 1.3- $\mu\text{m}$ In(Ga)As quantum-dot lasers. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2005</b> , 26, 382-385	3	6
252	The polaronic nature of intraband relaxation in InAs/GaAs self-assembled quantum dots. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2005</b> , 26, 408-412	3	5
251	Effect of the electron population on intraband absorption in InAs/GaAs self-assembled quantum dots. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2005</b> , 26, 105-109	3	12
250	Influence of In composition on the photoluminescence emission of In(Ga)As quantum dot bilayers. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2005</b> , 26, 124-128	3	2
249	Enhanced photoluminescence intensity of 1.3- $\mu\text{m}$ multi-layer InAs/InGaAs dots-in-well structure using the high growth temperature spacer layer step. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2005</b> , 26, 129-132	3	2
248	Anomalous Stark shifts in single vertically coupled pairs of InGaAs quantum dots. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2005</b> , 26, 302-307	3	6
247	Anisotropy of the electron energy levels in $\text{In}_x\text{Ga}_{1-x}\text{As}/\text{GaAs}$ quantum dots with non uniform composition. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2005</b> , 26, 436-440	3	11
246	Strain interactions and defect formation in stacked InGaAs quantum dot and dot-in-well structures. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2005</b> , 26, 245-251	3	10
245	Structural and optical properties of high In and N content GaInNAs quantum wells. <i>Thin Solid Films</i> , <b>2005</b> , 483, 185-190	2.2	5
244	Surface elemental segregation and the Stranski-Krastanow epitaxial islanding transition. <i>Applied Surface Science</i> , <b>2005</b> , 244, 65-70	6.7	15



243	Observation of a low Curie temperature ferromagnetic phase of ultrathin epitaxial Fe films on GaAs(0 0 1). <i>Journal of Magnetism and Magnetic Materials</i> , <b>2005</b> , 292, 241-247	2.8	6
242	Optimizing the growth of 1.3- $\mu\text{m}$ InAs/InGaAs dots-in-a-well structure: Achievement of high-performance laser. <i>Materials Science and Engineering C</i> , <b>2005</b> , 25, 779-783	8.3	9
241	Critical barrier thickness for the formation of InGaAs/GaAs quantum dots. <i>Materials Science and Engineering C</i> , <b>2005</b> , 25, 798-803	8.3	4
240	Characterization of structure and defects in dot-in-well laser structures. <i>Materials Science and Engineering C</i> , <b>2005</b> , 25, 793-797	8.3	1
239	Spinodal decomposition in GaInNAs/GaAs multi-quantum wells. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2005</b> , 2, 1292-1297		
238	Capacitance-voltage measurements in InAs-GaAs self-assembled quantum dots. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2005</b> , 2, 3163-3166		1
237	Growth, Fabrication, and Operating Characteristics of Ultra-Low Threshold Current Density 1.3 $\mu\text{m}$ Quantum Dot Lasers. <i>Japanese Journal of Applied Physics</i> , <b>2005</b> , 44, 2520-2522	1.4	11
236	Reflection and emission of Brillouin zone edge states for active photonic crystal waveguides. <i>Journal of Optics</i> , <b>2005</b> , 7, S270-S275		
235	Photoluminescence spectroscopy of bandgap reduction in dilute InNAs alloys. <i>Applied Physics Letters</i> , <b>2005</b> , 87, 182114	3.4	47
234	Tuning of electronic coupling between self-assembled quantum dots. <i>Applied Physics Letters</i> , <b>2005</b> , 87, 033104	3.4	3
233	Concentration dependent interdiffusion in InGaAs/GaAs as evidenced by high resolution x-ray diffraction and photoluminescence spectroscopy. <i>Journal of Applied Physics</i> , <b>2005</b> , 97, 013536	2.5	8
232	Breakup of the conduction band structure of dilute GaAs <sub>1-x</sub> Ny alloys. <i>Physical Review B</i> , <b>2005</b> , 71,	3.3	39
231	Enhanced optical and structural properties of 1.3- $\mu\text{m}$ GaInNAs/GaAs multiple quantum-well heterostructures with stepped strain-mediating layers. <i>Applied Physics Letters</i> , <b>2005</b> , 86, 062107	3.4	1
230	Effect of hydrostatic pressure on the fragmented conduction band structure of dilute Ga(AsN) alloys. <i>Physical Review B</i> , <b>2005</b> , 72,	3.3	20
229	Mapping quantum dot-in-well structures on the nanoscale using the plasmon peak in electron energy loss spectra. <i>Physical Review B</i> , <b>2005</b> , 72,	3.3	20
228	Optical orientation and control of spin memory in individual InGaAs quantum dots. <i>Physical Review B</i> , <b>2005</b> , 72,	3.3	42
227	Composition modulation in GaInNAs quantum wells: Comparison of experiment and theory. <i>Journal of Applied Physics</i> , <b>2005</b> , 97, 073705	2.5	12
226	Long-wavelength light emission and lasing from InAs/GaAs quantum dots covered by a GaAsSb strain-reducing layer. <i>Applied Physics Letters</i> , <b>2005</b> , 86, 143108	3.4	111

225	Individual neutral and charged $\text{In}_x\text{Ga}_{1-x}\text{As}/\text{GaAs}$ quantum dots with strong in-plane optical anisotropy. <i>Physical Review B</i> , <b>2005</b> , 72,	3.3	52
224	Influence of growth temperature on the structural and optical quality of $\text{GaInNAs}/\text{GaAs}$ multi-quantum wells. <i>Semiconductor Science and Technology</i> , <b>2004</b> , 19, 813-818	1.8	20
223	Electron spectroscopy of dilute nitrides. <i>Journal of Physics Condensed Matter</i> , <b>2004</b> , 16, S3201-S3214	1.8	7
222	Carrier distribution, spontaneous emission, and gain in self-assembled quantum dot lasers <b>2004</b> , 5365, 86		3
221	Influence of composition on the piezoelectric effect and on the conduction band energy levels of $\text{In}_x\text{Ga}_{1-x}\text{As}/\text{GaAs}$ quantum dots. <i>Journal of Applied Physics</i> , <b>2004</b> , 96, 5169-5172	2.5	22
220	$\text{InGaAs}/\text{AlAsSb}$ quantum cascade lasers. <i>Applied Physics Letters</i> , <b>2004</b> , 85, 3992-3994	3.4	47
219	Temperature-induced carrier escape processes studied in absorption of individual $\text{In}_x\text{Ga}_{1-x}\text{As}$ quantum dots. <i>Physical Review B</i> , <b>2004</b> , 69,	3.3	17
218	Fuchs-Kliener phonon excitations in $\text{GaNAs}$ alloys. <i>Journal of Applied Physics</i> , <b>2004</b> , 95, 8466-8468	2.5	1
217	Laser dynamics in self-pulsating quantum dot systems. <i>Journal of Applied Physics</i> , <b>2004</b> , 95, 1036-1041	2.5	12
216	Precise measurement of the fraction of charged dots in self-assembled quantum dot ensembles using ultrafast pump-probe techniques. <i>Applied Physics Letters</i> , <b>2004</b> , 85, 2226-2228	3.4	6
215	Improved performance of 1.3 $\mu\text{m}$ multilayer $\text{InAs}$ quantum-dot lasers using a high-growth-temperature $\text{GaAs}$ spacer layer. <i>Applied Physics Letters</i> , <b>2004</b> , 85, 704-706	3.4	221
214	Direct observation of LO phonon-plasmon coupled modes in the infrared transmission spectra of $n\text{-GaAs}$ and $n\text{-In}_x\text{Ga}_{1-x}\text{As}$ epilayers. <i>Physical Review B</i> , <b>2004</b> , 69,	3.3	21
213	Dynamics of coherent and incoherent spin polarizations in ensembles of quantum dots. <i>Physical Review Letters</i> , <b>2004</b> , 93, 057401	7.4	66
212	4.3 $\mu\text{m}$ intersubband emission from $\text{InGaAs}/\text{AlAsSb}$ quantum cascade structures. <i>Applied Physics Letters</i> , <b>2004</b> , 84, 1447-1449	3.4	17
211	Optical characteristics of 1.55 $\mu\text{m}$ $\text{GaInNAs}$ multiple quantum wells. <i>Applied Physics Letters</i> , <b>2004</b> , 85, 4013-4015	3.4	21
210	Influences of the spacer layer growth temperature on multilayer $\text{InAs}/\text{GaAs}$ quantum dot structures. <i>Journal of Applied Physics</i> , <b>2004</b> , 96, 1988-1992	2.5	74
209	Core-level photoemission spectroscopy of nitrogen bonding in $\text{GaN}_x\text{As}_{1-x}$ alloys. <i>Applied Physics Letters</i> , <b>2004</b> , 85, 1550-1552	3.4	27
208	Measurements of optical losses in mid-infrared semiconductor lasers using Fabry-Pérot transmission oscillations. <i>Journal of Applied Physics</i> , <b>2004</b> , 95, 7584-7587	2.5	14

207	Investigations of 1.55- $\mu\text{m}$ GaInNAs/GaAs heterostructures by optical spectroscopy. <i>IEE Proceedings: Optoelectronics</i> , <b>2004</b> , 151, 331-334		2
206	Structural defects characterisation of GaInNAs MQWs by TEM and PL. <i>IEE Proceedings: Optoelectronics</i> , <b>2004</b> , 151, 385-388		3
205	Composition fluctuations in GaInNAs multi-quantum wells. <i>IEE Proceedings: Optoelectronics</i> , <b>2004</b> , 151, 271-274		
204	Improvement in the optical quality of GaInNAs/GaInAs quantum well structures by interfacial strain reduction. <i>IEE Proceedings: Optoelectronics</i> , <b>2004</b> , 151, 301-304		2
203	Probing the N-induced states in dilute GaAsN alloys by magneto-tunnelling. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2004</b> , 21, 892-896		3
202	High pressure as a tool to tune electronic coupling in self-assembled quantum dot nanostructures. <i>Physica Status Solidi (B): Basic Research</i> , <b>2004</b> , 241, 3257-3262	1.3	2
201	AlAs-like TO-phonon dephasing time in high Al content AlGaAs. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2004</b> , 1, 2686-2689		
200	Polaron decay and inter-level transfer in InAs/GaAs self-assembled quantum dots. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2004</b> , 1, 2613-2616		2
199	Mode formation in broad area quantum dot lasers at 1060 nm. <i>Optics Communications</i> , <b>2004</b> , 235, 387-393		4
198	Structural and optical quality of InGaAsN quantum wells grown on misoriented GaAs (1 1 1)b substrates by molecular beam epitaxy. <i>Journal of Crystal Growth</i> , <b>2004</b> , 270, 62-68	1.6	7
197	Systematic reduction of the permanent exciton dipole for charged excitons in individual self-assembled InGaAs quantum dots. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2004</b> , 21, 199-203	3	2
196	Polaron relaxation dynamics in InAs/GaAs self-assembled quantum dots. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2004</b> , 21, 405-408	3	13
195	Effect of thermal annealing and strain engineering on the fine structure of quantum dot excitons. <i>Physical Review B</i> , <b>2004</b> , 70,	3.3	73
194	Quantum-confined Stark shifts of charged exciton complexes in quantum dots. <i>Physical Review B</i> , <b>2004</b> , 70,	3.3	99
193	Anomalous dispersion with excitation wavelength of longitudinal optical phonon-plasmon coupled modes in n-InGaAs. <i>Journal of Physics Condensed Matter</i> , <b>2004</b> , 16, 971-978	1.8	
192	Intraband relaxation via polaron decay in InAs self-assembled quantum dots. <i>Physical Review B</i> , <b>2004</b> , 70,	3.3	94
191	Polaron relaxation channel in InAs/GaAs self-assembled quantum dots. <i>Semiconductor Science and Technology</i> , <b>2004</b> , 19, S316-S318	1.8	8
190	1.3 [ $\mu\text{m}$ ] InAs/GaAs multilayer quantum-dot laser with extremely low room-temperature threshold current density. <i>Electronics Letters</i> , <b>2004</b> , 40, 1412	1.1	104

189	Temperature dependence of carrier dynamics in an inhomogeneous array of quantum dots <b>2004</b> , 5452, 33		2
188	A ballistic electron emission microscopy study of ferromagnetic thin films embedded in Au/GaAs(100). <i>Journal of Physics Condensed Matter</i> , <b>2003</b> , 15, 6485-6492	1.8	2
187	The effect of dead space on gain and excess noise in In <sub>0.48</sub> Ga <sub>0.52</sub> P p-n diodes. <i>Semiconductor Science and Technology</i> , <b>2003</b> , 18, 803-806	1.8	21
186	Composition profiling at the atomic scale in III-V nanostructures by cross-sectional STM. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2003</b> , 17, 526-532	3	11
185	Observation of in-plane polarized intersublevel absorption in strongly coupled InGaAs/GaAs self assembled quantum dots. <i>Physica Status Solidi (B): Basic Research</i> , <b>2003</b> , 238, 341-344	1.3	4
184	Continuum transitions and phonon coupling in single self-assembled Stranski-Krastanow quantum dots. <i>Physical Review B</i> , <b>2003</b> , 68,	3.3	57
183	The onset of plasticity in nanoscale contact loading. <i>Proceedings of the Royal Society A: Mathematical, Physical and Engineering Sciences</i> , <b>2003</b> , 459, 2049-2068	2.4	23
182	Optimizing the growth of 1.3 eV InAs/InGaAs dots-in-a-well structure. <i>Journal of Applied Physics</i> , <b>2003</b> , 93, 2931-2936	2.5	154
181	Crack initiation and termination in III-V epitaxial layers. <i>Philosophical Magazine</i> , <b>2003</b> , 83, 3077-3092	1.6	3
180	Engineering carrier confinement potentials in 1.3-eV InAs/GaAs quantum dots with InAlAs layers: Enhancement of the high-temperature photoluminescence intensity. <i>Applied Physics Letters</i> , <b>2003</b> , 83, 3716-3718	3.4	37
179	Tuning the structural and optical properties of 1.3-eV InAs/GaAs quantum dots by a combined InAlAs and GaAs strained buffer layer. <i>Applied Physics Letters</i> , <b>2003</b> , 82, 3644-3646	3.4	33
178	Strong in-plane polarized intraband absorption in vertically aligned InGaAs/GaAs quantum dots. <i>Applied Physics Letters</i> , <b>2003</b> , 82, 3415-3417	3.4	26
177	Carrier dynamics in short wavelength self-assembled InAs/Al <sub>0.6</sub> Ga <sub>0.4</sub> As quantum dots with indirect barriers. <i>Journal of Applied Physics</i> , <b>2003</b> , 93, 3524-3528	2.5	16
176	Improving optical properties of 1.55 eV GaInNAs/GaAs multiple quantum wells with Ga(In)NAs barrier and space layer. <i>Applied Physics Letters</i> , <b>2003</b> , 83, 4951-4953	3.4	41
175	Spatially resolved scanning tunneling luminescence on self-assembled InGaAs/GaAs quantum dots. <i>Applied Physics Letters</i> , <b>2003</b> , 83, 290-292	3.4	10
174	Defect states and commensurability in dual-period Al <sub>x</sub> Ga <sub>1-x</sub> As photonic crystal waveguides. <i>Physical Review B</i> , <b>2003</b> , 68,	3.3	24
173	Demonstration of a blueshift in type II asymmetric InP/InAsP/InGaAs multiple quantum wells. <i>Journal of Applied Physics</i> , <b>2003</b> , 94, 3222-3228	2.5	5
172	Dilute nitride based double-barrier quantum-well infrared photodetector operating in the near infrared. <i>Applied Physics Letters</i> , <b>2003</b> , 83, 3111-3113	3.4	27

171	Magnetotunneling spectroscopy of dilute Ga(AsN) quantum wells. <i>Physical Review Letters</i> , <b>2003</b> , 91, 12680-12682	3.4	5
170	Metastable rocksalt phase in epitaxial GaN on sapphire. <i>Applied Physics Letters</i> , <b>2003</b> , 83, 2808-2810	3.4	5
169	On the diffusion of lattice matched InGaAs/InP microstructures. <i>Journal of Applied Physics</i> , <b>2003</b> , 93, 3881-3885	2.5	18
168	Stacked low-growth-rate InAs quantum dots studied at the atomic level by cross-sectional scanning tunneling microscopy. <i>Applied Physics Letters</i> , <b>2003</b> , 82, 3758-3760	3.4	53
167	1.3 $\mu$ m lasers with AlInAs-capped self-assembled quantum dots. <i>Applied Physics Letters</i> , <b>2003</b> , 83, 4710-4712	3.4	19
166	Comparison of intraband absorption and photocurrent in InAs/GaAs quantum dots. <i>Applied Physics Letters</i> , <b>2003</b> , 83, 602-604	3.4	28
165	Multiplication and excess noise in Al <sub>x</sub> Ga <sub>1-x</sub> As/GaAs multilayer avalanche photodiodes. <i>Journal of Applied Physics</i> , <b>2003</b> , 94, 2631-2637	2.5	10
164	Room-temperature operation of an InAs/GaAs/AlAs quantum-cascade laser. <i>Applied Physics Letters</i> , <b>2003</b> , 82, 3409-3411	3.4	19
163	Avalanche multiplication and breakdown in Al/sub x/Ga/sub 1-x/As (x IEEE Transactions on Electron Devices, <b>2002</b> , 49, 2349-2351	2.9	14
162	Optical properties of single charge tuneable InGaAs quantum dots. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2002</b> , 13, 127-130	3	11
161	Strategies for reducing the emission wavelength of GaAs/AlAs quantum cascade lasers. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2002</b> , 13, 835-839	3	
160	Determination of the outward relaxation of cleaved strained InAs structures by scanning tunneling microscopy. <i>Applied Surface Science</i> , <b>2002</b> , 190, 258-263	6.7	19
159	Characterisation of strained (111)B InGaAs/GaAs quantum well lasers with intracavity optical modulator. <i>Microelectronics Journal</i> , <b>2002</b> , 33, 547-552	1.8	6
158	Relaxation study of AlGaAs cladding layers in InGaAs/GaAs (111)B lasers designed for 1.0-1.1 $\mu$ m operation. <i>Microelectronics Journal</i> , <b>2002</b> , 33, 553-557	1.8	2
157	The role of climb and glide in misfit relief of InGaAs/GaAs(111)B heterostructures. <i>Microelectronics Journal</i> , <b>2002</b> , 33, 559-563	1.8	
156	Comparative study of InGaAs quantum dot lasers with different degrees of dot layer confinement. <i>Applied Physics Letters</i> , <b>2002</b> , 81, 1-3	3.4	64
155	Strain relaxation behavior of In <sub>x</sub> Ga <sub>1-x</sub> As quantum wells on vicinal GaAs (111)B substrates. <i>Applied Physics Letters</i> , <b>2002</b> , 80, 1541-1543	3.4	6
154	Stranski-Krastanow transition and epitaxial island growth. <i>Physical Review B</i> , <b>2002</b> , 66,	3.3	109

153	Temperature dependence of avalanche multiplication in submicron Al <sub>0.6</sub> Ga <sub>0.4</sub> As diodes. <i>Journal of Applied Physics</i> , <b>2002</b> , 92, 7684-7686	2.5	19
152	Dynamics of stimulated emission in InAs quantum-dot laser structures measured in pump-probe experiments. <i>Applied Physics Letters</i> , <b>2002</b> , 81, 4118-4120	3.4	2
151	Filamentation and linewidth enhancement factor in InGaAs quantum dot lasers. <i>Applied Physics Letters</i> , <b>2002</b> , 81, 3251-3253	3.4	56
150	GaAs-based quantum cascade lasers with native oxide-defined current confinement. <i>Electronics Letters</i> , <b>2002</b> , 38, 75	1.1	
149	Room temperature GaAs-based quantum cascade laser with GaInP waveguide cladding. <i>Electronics Letters</i> , <b>2002</b> , 38, 1539	1.1	7
148	Intervalley scattering in GaAs/AlAs quantum cascade lasers. <i>Applied Physics Letters</i> , <b>2002</b> , 81, 1378-1380	3.4	30
147	Experimental investigation of the effect of wetting-layer states on the gain-current characteristic of quantum-dot lasers. <i>Applied Physics Letters</i> , <b>2002</b> , 81, 4904-4906	3.4	162
146	Excess noise characteristics of Al <sub>0.8</sub> /Ga <sub>0.2</sub> /As avalanche photodiodes. <i>IEEE Photonics Technology Letters</i> , <b>2002</b> , 14, 522-524	2.2	20
145	Determination of the shape and indium distribution of low-growth-rate InAs quantum dots by cross-sectional scanning tunneling microscopy. <i>Applied Physics Letters</i> , <b>2002</b> , 81, 1708-1710	3.4	184
144	Fine structure of charged and neutral excitons in InAs-Al <sub>0.6</sub> Ga <sub>0.4</sub> As quantum dots. <i>Physical Review B</i> , <b>2002</b> , 66,	3.3	103
143	Cracking self-assembled InAs quantum dots. <i>Applied Physics A: Materials Science and Processing</i> , <b>2001</b> , 72, S205-S207	2.6	9
142	Fermi-edge singularities in a one-dimensional electron system in magnetic field. <i>Solid State Communications</i> , <b>2001</b> , 119, 55-58	1.6	1
141	Effect of graded buffer design on the defect structure in InGaAs/GaAs (111)B heterostructures. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2001</b> , 80, 27-31	3.1	4
140	Electronic properties of InAs/GaAs self-assembled quantum dots studied by photocurrent spectroscopy. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2001</b> , 9, 106-113	3	13
139	Temperature Dependent Optical Properties of InAs/AlGaAs Quantum Dots. <i>Physica Status Solidi (B): Basic Research</i> , <b>2001</b> , 224, 107-110	1.3	1
138	Optical Spectroscopic Study of Carrier Processes in Self-Assembled In(Ga)As/AlGaAs Quantum Dot Lasers. <i>Physica Status Solidi (B): Basic Research</i> , <b>2001</b> , 224, 123-127	1.3	2
137	Excitation and Relaxation Mechanisms in Single In(Ga)As Quantum Dots. <i>Physica Status Solidi (B): Basic Research</i> , <b>2001</b> , 224, 373-378	1.3	4
136	Recombination of Many-Particle States in InAs Self-Organized Quantum Dots. <i>Physica Status Solidi (B): Basic Research</i> , <b>2001</b> , 224, 409-412	1.3	4

135	Photocurrent Spectroscopy of InAs/GaAs Self-Assembled Quantum Dots. <i>Physica Status Solidi (B): Basic Research</i> , <b>2001</b> , 224, 497-502	1.3	6
134	Avalanche multiplication characteristics of Al/sub 0.8/Ga/sub 0.2/As diodes. <i>IEEE Transactions on Electron Devices</i> , <b>2001</b> , 48, 2198-2204	2.9	30
133	Al <sub>0.8</sub> Ga <sub>0.2</sub> As: A very low excess noise multiplication medium for avalanche photodiodes. <i>IEE Proceedings: Optoelectronics</i> , <b>2001</b> , 148, 243-246		
132	Performance of lasers containing three, five and seven layers of quantum dots. <i>IEE Proceedings: Optoelectronics</i> , <b>2001</b> , 148, 238-242		3
131	Thermodynamic balance in quantum dot lasers. <i>Semiconductor Science and Technology</i> , <b>2001</b> , 16, 140-143	1.8	41
130	Electrically pumped InGaAs quantum dot ring and cylindrical cavity lasers. <i>Electronics Letters</i> , <b>2001</b> , 37, 1220	1.1	2
129	Indium segregation in (111)B GaAs-In <sub>x</sub> Ga <sub>1-x</sub> As quantum wells determined by transmission electron microscopy. <i>Journal Physics D: Applied Physics</i> , <b>2001</b> , 34, 1943-1946	3	9
128	Optical mode loss and gain of multiple-layer quantum-dot lasers. <i>Applied Physics Letters</i> , <b>2001</b> , 78, 2629-2631	3.4	41
127	Temperature dependence of the lasing wavelength of InGaAs quantum dot lasers. <i>Journal of Applied Physics</i> , <b>2001</b> , 90, 4859-4861	2.5	16
126	Intensity noise in quantum-dot laser diodes. <i>Applied Physics Letters</i> , <b>2001</b> , 78, 3577-3579	3.4	4
125	Decreasing the emission wavelength of GaAs/AlGaAs quantum cascade lasers by the incorporation of ultrathin InGaAs layers. <i>Applied Physics Letters</i> , <b>2001</b> , 78, 413-415	3.4	18
124	Observation of multicharged excitons and biexcitons in a single InGaAs quantum dot. <i>Physical Review B</i> , <b>2001</b> , 63,	3.3	132
123	Structural and optical studies of vertically aligned InAs/GaAs self-assembled quantum dots. <i>Journal of Applied Physics</i> , <b>2001</b> , 90, 6374-6378	2.5	36
122	Raman scattering by LO phonon-plasmon coupled modes in n-type In <sub>0.53</sub> Ga <sub>0.47</sub> As. <i>Physical Review B</i> , <b>2001</b> , 65,	3.3	29
121	Nature of the Stranski-Krastanow transition during epitaxy of InGaAs on GaAs. <i>Physical Review Letters</i> , <b>2001</b> , 86, 2381-4	7.4	220
120	Enhanced phonon-assisted absorption in single InAs/GaAs quantum dots. <i>Physical Review B</i> , <b>2001</b> , 63,	3.3	84
119	8.3 [micro sign]m GaAs/AlAs quantum cascade lasers incorporating InAs monolayers. <i>Electronics Letters</i> , <b>2001</b> , 37, 1292	1.1	8
118	Charged and neutral exciton complexes in individual self-assembled In(Ga)As quantum dots. <i>Physical Review B</i> , <b>2001</b> , 63,	3.3	158

117	Strained layer (111)B GaAs/InGaAs single quantum well lasers and the dependence of their characteristics upon indium composition. <i>Journal of Applied Physics</i> , <b>2001</b> , 89, 4689-4696	2.5	15
116	Epitaxial Island Growth and the Stranski-Krastanow Transition. <i>Materials Research Society Symposia Proceedings</i> , <b>2001</b> , 696, 1		
115	Shape analysis of single and stacked InAs quantum dots at the atomic level by cross-sectional STM. <i>Springer Proceedings in Physics</i> , <b>2001</b> , 359-360	0.2	
114	Temperature Dependent Optical Properties of InAs/AlGaAs Quantum Dots <b>2001</b> , 224, 107		1
113	Quantum Confined Stark Effect and Permanent Dipole Moment of InAs/GaAs Self-Assembled Quantum Dots. <i>Physica Status Solidi A</i> , <b>2000</b> , 178, 269-275		6
112	Dynamical Band Gap Renormalization in Self-Organized InAs/GaAs Quantum Dots. <i>Physica Status Solidi A</i> , <b>2000</b> , 178, 345-348		4
111	Static and growing InP and InAs surfaces: reflection-anisotropy spectroscopy under the conditions of solid-source MBE. <i>Thin Solid Films</i> , <b>2000</b> , 364, 6-11	2.2	6
110	Electronic structure of InAs/GaAs self-assembled quantum dots studied by perturbation spectroscopy. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2000</b> , 6, 348-357	3	8
109	Improved performance from GaAs/AlGaAs quantum cascade lasers with enhanced upper laser level confinement. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2000</b> , 7, 8-11	3	3
108	Photocurrent spectroscopy of InAs/GaAs self-assembled quantum dots: observation of a permanent dipole moment. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2000</b> , 7, 408-412	3	5
107	InAs/GaAs self-assembled quantum dot lasers: physical processes and device characteristics. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2000</b> , 7, 489-493	3	3
106	General characteristics of crack arrays in epilayers grown under tensile strain. <i>Semiconductor Science and Technology</i> , <b>2000</b> , 15, 325-330	1.8	19
105	Modal gain and lasing states in InAs/GaAs self-organized quantum dot lasers. <i>Journal of Applied Physics</i> , <b>2000</b> , 87, 615-617	2.5	18
104	Modal gain and internal optical mode loss of a quantum dot laser. <i>Applied Physics Letters</i> , <b>2000</b> , 77, 163-165	3.5	26
103	Electric-field-dependent carrier capture and escape in self-assembled InAs/GaAs quantum dots. <i>Applied Physics Letters</i> , <b>2000</b> , 77, 4344-4346	3.4	77
102	Photocurrent spectroscopy of InAs/GaAs self-assembled quantum dots. <i>Physical Review B</i> , <b>2000</b> , 62, 16784-16791	3.5	79
101	Impact ionization coefficients of Al <sub>0.8</sub> Ga <sub>0.2</sub> As. <i>Applied Physics Letters</i> , <b>2000</b> , 77, 4374-4376	3.4	18
100	Inverted electron-hole alignment in InAs-GaAs self-assembled quantum dots. <i>Physical Review Letters</i> , <b>2000</b> , 84, 733-6	7.4	433



99	Electronic Properties of InAs/GaAs Self-Assembled Quantum Dot Structures and Devices Studied by Photocurrent Spectroscopy. <i>Acta Physica Polonica A</i> , <b>2000</b> , 98, 279-293	0.6	1
98	The Stark Effect and Electron-Hole Wavefunctions in InAs-GaAs Self-Assembled Quantum Dots <b>2000</b> , 337-346		
97	Comparison of performance of GaAs-AlGaAs and InGaAs-AlInAs quantum cascade lasers. <i>Electronics Letters</i> , <b>1999</b> , 35, 2034	1.1	7
96	Gain characteristics of InAs/GaAs self-organized quantum-dot lasers. <i>Applied Physics Letters</i> , <b>1999</b> , 75, 3512-3514	3.4	18
95	Many-body effects in carrier capture and energy relaxation in self-organized InAs/GaAs quantum dots. <i>Physica B: Condensed Matter</i> , <b>1999</b> , 272, 12-14	2.8	25
94	Optical properties of In <sub>x</sub> Ga <sub>1-x</sub> As/GaAs MQW structures on (1 1 1)B GaAs grown by MBE: dependence on substrate miscut. <i>Journal of Crystal Growth</i> , <b>1999</b> , 201-202, 1085-1088	1.6	3
93	Relaxation study of In <sub>x</sub> Ga <sub>1-x</sub> As/GaAs quantum-well structures grown by MBE on (001) and (111)B GaAs for long wavelength applications. <i>Journal of Crystal Growth</i> , <b>1999</b> , 206, 287-293	1.6	4
92	Influence of substrate misorientation on the structural characteristics of InGaAs/GaAs MQW on (111)B GaAs grown by MBE. <i>Thin Solid Films</i> , <b>1999</b> , 343-344, 558-561	2.2	3
91	Excited States in Self-Assembled InAs/GaAs Quantum Dots under High Pressure. <i>Physica Status Solidi (B): Basic Research</i> , <b>1999</b> , 211, 73-77	1.3	6
90	Photoluminescence decay time measurements from self-organized InAs/GaAs quantum dots. <i>Journal of Applied Physics</i> , <b>1999</b> , 86, 2555-2561	2.5	72
89	Excited states and selection rules in self-assembled InAs/GaAs quantum dots. <i>Physical Review B</i> , <b>1999</b> , 60, R2185-R2188	3.3	57
88	Photocurrent Spectroscopy of InAs/GaAs Self-Assembled Quantum Dots: Observation of a Permanent Dipole Moment. <i>Materials Research Society Symposia Proceedings</i> , <b>1999</b> , 571, 147		
87	Structural and morphological characteristics of InGaAs/GaAs quantum well structures on tilted (111)B GaAs grown by MBE. <i>Journal of Crystal Growth</i> , <b>1998</b> , 192, 363-371	1.6	4
86	Avalanche multiplication and breakdown in Ga/sub 0.52/In/sub 0.48/P diodes. <i>IEEE Transactions on Electron Devices</i> , <b>1998</b> , 45, 2096-2101	2.9	18
85	1.3 μm InAsP quantum well lasers grown by solid source MBE. <i>IEE Proceedings: Optoelectronics</i> , <b>1998</b> , 145, 3-6		4
84	Light sources for wavelengths > 2 μm grown by MBE on InP using a strain relaxed buffer. <i>IEE Proceedings: Optoelectronics</i> , <b>1998</b> , 145, 292-296		10
83	Investigation of delta-doped quantum wells for power FET applications. <i>Superlattices and Microstructures</i> , <b>1998</b> , 23, 187-190	2.8	4
82	Inversion of electron sub-band population in a GaAs/AlGaAs triple barrier tunnelling structure. <i>Solid-State Electronics</i> , <b>1998</b> , 42, 1533-1537	1.7	1

81	Strain-induced quantum confinement of electron gases. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>1998</b> , 2, 272-276	3	
80	Population inversion and intersubband electroluminescence in GaAs/AlGaAs triple barrier tunnelling structures. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>1998</b> , 2, 473-477	3	
79	Magneto-optical spectroscopy of InAs/GaAs self-organised quantum dots. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>1998</b> , 2, 689-693	3	
78	Surface structure of InP(001) under dynamic and static conditions of molecular beam epitaxy. <i>Applied Surface Science</i> , <b>1998</b> , 123-124, 313-318	6.7	7
77	Magneto-optical studies of self-organized InAs/GaAs quantum dots. <i>Physical Review B</i> , <b>1998</b> , 57, R2073-R2076	3.9	41
76	Emission spectra and mode structure of InAs/GaAs self-organized quantum dot lasers. <i>Applied Physics Letters</i> , <b>1998</b> , 73, 969-971	3.4	134
75	2.7 [micro sign]m LEDs for water vapour detection grown by MBE on InP. <i>Electronics Letters</i> , <b>1998</b> , 34, 1606	1.1	4
74	Optical properties of (Al <sub>x</sub> Ga <sub>1-x</sub> ) <sub>0.52</sub> In <sub>0.48</sub> P at the crossover from a direct-gap to an indirect-gap semiconductor. <i>Journal of Applied Physics</i> , <b>1998</b> , 83, 2241-2249	2.5	6
73	Optical monitoring of InP monolayer growth rates. <i>Applied Physics Letters</i> , <b>1998</b> , 73, 345-347	3.4	3
72	Phase-matched second harmonic generation in asymmetric double quantum wells. <i>Applied Physics Letters</i> , <b>1998</b> , 72, 2654-2656	3.4	27
71	Reflectance anisotropy spectroscopy study of the surface reconstructions of decapped InP(001). <i>Journal of Applied Physics</i> , <b>1998</b> , 83, 480-485	2.5	11
70	Mid-infrared intersubband electroluminescence from a single-period GaAs/AlGaAs triple barrier structure. <i>Applied Physics Letters</i> , <b>1998</b> , 72, 2141-2143	3.4	7
69	Photoluminescence spectroscopy of intersubband population inversion in a GaAs/Al <sub>x</sub> Ga <sub>1-x</sub> As triple-barrier tunneling structure. <i>Physical Review B</i> , <b>1998</b> , 57, 6290-6293	3.3	16
68	Strain-induced quantum confinement of electron gases: The observation of quantum dot levels. <i>Applied Physics Letters</i> , <b>1998</b> , 73, 1898-1900	3.4	4
67	Carrier lifetime and exciton saturation in a strain-balanced InGaAs/InAsP multiple quantum well. <i>Journal of Applied Physics</i> , <b>1998</b> , 83, 306-309	2.5	4
66	Impact ionization coefficients in GaInP p-i-n diodes. <i>Applied Physics Letters</i> , <b>1997</b> , 70, 3567-3569	3.4	17
65	Coherency Strain as an Athermal Strengthening Mechanism. <i>Physical Review Letters</i> , <b>1997</b> , 78, 3912-3914	4.4	19
64	Optical spectroscopic determination of the electronic band structure of bulk AlGaInP and GaInP-AlGaInP heterojunction band offsets <b>1997</b> ,		1

63	As/P exchange on InP(001) studied by reflectance anisotropy spectroscopy. <i>Applied Physics Letters</i> , <b>1997</b> , 70, 1423-1425	3.4	27
62	In situ monitoring of the surface reconstructions on InP(001) prepared by molecular beam epitaxy. <i>Journal of Applied Physics</i> , <b>1997</b> , 82, 474-476	2.5	59
61	Magneto-optics of zero-dimensional electron systems. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>1997</b> , 1, 191-197	3	1
60	Incorporation of As <sub>2</sub> in InAs <sub>x</sub> P <sub>1-x</sub> and its application to quantum well structures. <i>Journal of Crystal Growth</i> , <b>1997</b> , 175-176, 1033-1038	1.6	4
59	Photoconductivity studies of InAsP/InP heterostructures in applied magnetic and electric fields. <i>Semiconductor Science and Technology</i> , <b>1996</b> , 11, 34-38	1.8	3
58	Optical spectroscopic observation of spontaneous long range ordering in AlGaInP. <i>Applied Physics Letters</i> , <b>1996</b> , 68, 3266-3268	3.4	12
57	Voltage enhancement in quantum well solar cells. <i>Journal of Applied Physics</i> , <b>1996</b> , 80, 1201-1206	2.5	59
56	Investigation of g-factors Zeeman splittings, exchange interactions and field-dependent spin relaxation in III-V quantum wells. <i>Surface Science</i> , <b>1996</b> , 361-362, 435-438	1.8	4
55	Electronic energy levels and energy relaxation mechanisms in self-organized InAs/GaAs quantum dots. <i>Physical Review B</i> , <b>1996</b> , 54, 17738-17744	3.3	152
54	Wannier-Stark ladder spectra in In <sub>x</sub> Ga <sub>1-x</sub> As/GaAs strained layer piezo-electric superlattices. <i>Solid-State Electronics</i> , <b>1996</b> , 40, 167-170	1.7	
53	Low-temperature mobility of two-dimensional electrons in (Ga,In)As/(Al,In)As heterojunctions. <i>Journal of Applied Physics</i> , <b>1996</b> , 79, 8465-8469	2.5	6
52	Crack formation in III-V epilayers grown under tensile strain on InP(001) substrates. <i>Philosophical Magazine A: Physics of Condensed Matter, Structure, Defects and Mechanical Properties</i> , <b>1996</b> , 74, 383-393		25
51	Study of a backgated metal-semiconductor-metal photodetector. <i>Applied Physics Letters</i> , <b>1996</b> , 68, 815-817	3.1	8
50	Mobility and saturation drift velocity enhancement in highly doped GaAs and In <sub>x</sub> Ga <sub>1-x</sub> As structures designed for use in power FET devices. <i>Electronics Letters</i> , <b>1996</b> , 32, 494	1.1	5
49	Visible vertical cavity surface emitting lasers at [Materials Science and Engineering B: Solid-State Materials for Advanced Technology, <b>1995</b> , 35, 12-16	3.1	2
48	In <sub>x</sub> Ga <sub>1-x</sub> As/InP quantum well structures grown on [111]B InP. <i>Microelectronics Journal</i> , <b>1995</b> , 26, 805-810	1.8	10
47	Band gap of [completely disordered]Ga <sub>0.52</sub> In <sub>0.48</sub> P. <i>Applied Physics Letters</i> , <b>1995</b> , 66, 3185-3187	3.4	42
46	GaInP/AlGaInP band offsets determined from hydrostatic pressure measurements. <i>Applied Physics Letters</i> , <b>1995</b> , 66, 619-621	3.4	13

45	Observation of Wannier-Stark ladder transitions in $\text{In}_x\text{Ga}_{1-x}\text{As}$ -GaAs piezoelectric superlattices. <i>Physical Review B</i> , <b>1995</b> , 52, 14340-14343	3.3	5
44	Growth of $\text{InAs}_x\text{P}_{1-x}/\text{InP}$ multi-quantum well structures by solid source molecular beam epitaxy. <i>Journal of Applied Physics</i> , <b>1995</b> , 78, 3330-3334	2.5	14
43	Conduction band discontinuities in $\text{Ga}_{0.5}\text{In}_{0.5}\text{P}$ - $\text{Al}_x\text{Ga}_{0.5-x}\text{In}_{0.5}\text{P}$ heterojunctions measured by internal photoemission. <i>Applied Physics Letters</i> , <b>1995</b> , 66, 2852-2854	3.4	10
42	Enhanced mobility piezoelectric $\text{AlInAs}/\text{InGaAs}$ quantum well structures on (111)B InP substrates. <i>Electronics Letters</i> , <b>1995</b> , 31, 2215-2216	1.1	1
41	A comparison of 1.55 $\mu\text{m}$ distributed Bragg reflector stacks for use in multi quantum well micro resonator modulators. <i>Semiconductor Science and Technology</i> , <b>1995</b> , 10, 1283-1286	1.8	3
40	Exciton effects in strain-balanced $\text{GaInAs}/\text{AlInAs}$ and $\text{GaInAs}/\text{GaInAs}$ coupled quantum wells. <i>Nuovo Cimento Della Societa Italiana Di Fisica D - Condensed Matter, Atomic, Molecular and Chemical Physics, Biophysics</i> , <b>1995</b> , 17, 1607-1612		
39	Application of anodic oxidation for postgrowth tailoring of $\text{InGaAsP}/\text{InP}$ asymmetric Fabry-Perot modulator reflection spectra. <i>Electronics Letters</i> , <b>1995</b> , 31, 1186	1.1	3
38	Delta-doping-enhanced $\text{InGaAs}/\text{InAlAs}$ heterobarrier diodes. <i>Electronics Letters</i> , <b>1995</b> , 31, 493-494	1.1	
37	Highly doped 1.55 $\mu\text{m}$ $\text{Ga}_x\text{In}_{1-x}\text{As}/\text{InP}$ distributed Bragg reflector stacks. <i>Electronics Letters</i> , <b>1994</b> , 30, 1526-1527	1.1	6
36	Avalanche breakdown in $(\text{Al}_x\text{Ga}_{1-x})_{0.52}\text{In}_{0.48}\text{P}$ pin junctions. <i>Electronics Letters</i> , <b>1994</b> , 30, 907	1.1	4
35	Magnetic field effects on $\text{InP}/\text{InGaAs}$ quasiballistic heterojunction bipolar transistors. <i>Semiconductor Science and Technology</i> , <b>1994</b> , 9, 1153-1155	1.8	
34	Solid-source molecular beam epitaxy growth of $\text{GaInP}$ and $\text{GaInP}$ -containing quantum wells. <i>Journal of Applied Physics</i> , <b>1994</b> , 75, 2029-2034	2.5	20
33	Electronic band structure of $\text{AlGaInP}$ grown by solid-source molecular-beam epitaxy. <i>Applied Physics Letters</i> , <b>1994</b> , 65, 213-215	3.4	52
32	Optical spectroscopy of $\text{AlGaInP}$ based wide band gap quantum wells. <i>Superlattices and Microstructures</i> , <b>1994</b> , 15, 313	2.8	18
31	Measurement of the direct energy gap of $\text{Al}_{0.5}\text{In}_{0.5}\text{P}$ : Implications for the band discontinuity at $\text{Ga}_{1-x}\text{In}_x\text{P}/\text{Al}_y\text{In}_{1-y}\text{P}$ heterojunctions. <i>Physical Review B</i> , <b>1994</b> , 50, 11190-11191	3.3	11
30	Electroabsorption modulation in strained piezoelectric $\text{InGaAs}/\text{InP}$ multi-quantum wells operating at 1.55 $\mu\text{m}$ . <i>Electronics Letters</i> , <b>1994</b> , 30, 1707-1708	1.1	7
29	Photoluminescence, photoluminescence excitation, and resonant Raman spectroscopy of disordered and ordered $\text{Ga}_{0.52}\text{In}_{0.48}\text{P}$ . <i>Journal of Applied Physics</i> , <b>1993</b> , 73, 5163-5172	2.5	69
28	All-solid-state subpicosecond passively mode locked erbium-doped fiber laser. <i>Applied Physics Letters</i> , <b>1993</b> , 63, 4-6	3.4	27

27	High reflectivity and low resistance 1.55 $\mu$ m Al <sub>0.65</sub> In <sub>0.35</sub> As/Ga <sub>0.63</sub> In <sub>0.37</sub> As strained quarter wave Bragg reflector stack. <i>Electronics Letters</i> , <b>1993</b> , 29, 1947	1.1	6
26	. <i>IEEE Photonics Technology Letters</i> , <b>1993</b> , 5, 35-37	2.2	23
25	Transient photoluminescence in GaInAs/InP multiple quantum wells. <i>Semiconductor Science and Technology</i> , <b>1993</b> , 8, 1758-1763	1.8	1
24	Submilliwatt optical bistability in a coated InGaAs/InP multiquantum well waveguide FabryPerot cavity. <i>Electronics Letters</i> , <b>1993</b> , 29, 1537	1.1	3
23	Microstructure and cathodoluminescence of MBE-grown (001) In <sub>x</sub> Ga <sub>1-x</sub> P/GaAs strained-layer heterostructures. <i>Semiconductor Science and Technology</i> , <b>1993</b> , 8, 502-508	1.8	16
22	Carrier lifetimes in MBE and MOCVD InGaAs quantum wells. <i>Semiconductor Science and Technology</i> , <b>1993</b> , 8, 307-309	1.8	18
21	Optical bistability in an InGaAs/InP multiple quantum well waveguide FabryPerot cavity. <i>Applied Physics Letters</i> , <b>1993</b> , 63, 1610-1612	3.4	6
20	Guided-wave measurements of real-excitation optical nonlinearities in a tensile strained InGaAs on InP quantum well at 1.5 $\mu$ m. <i>Optics Communications</i> , <b>1993</b> , 102, 473-477	2	5
19	Asymmetric characteristics of InGaP/GaAs double-heterojunction bipolar transistors grown by solid source molecular beam epitaxy. <i>Semiconductor Science and Technology</i> , <b>1992</b> , 7, 425-428	1.8	6
18	Growth of strained InAs/InP quantum wells by molecular beam epitaxy. <i>Applied Physics Letters</i> , <b>1992</b> , 60, 841-843	3.4	22
17	Quasiballistic electron transport in InP/InGaAs heterojunction bipolar transistors. <i>Electronics Letters</i> , <b>1992</b> , 28, 145	1.1	3
16	Conduction-band discontinuity in InGaP/GaAs measured using both current-voltage and photoemission methods. <i>Applied Physics Letters</i> , <b>1992</b> , 60, 474-476	3.4	48
15	On the low-temperature efficiency of photoluminescence in a-Si: H and other materials. <i>The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties</i> , <b>1991</b> , 63, 179-191		5
14	Quantum-confined Stark effect in InGaAs/InP multiple quantum wells grown by solid source molecular beam epitaxy. <i>Journal of Crystal Growth</i> , <b>1991</b> , 111, 1080-1083	1.6	3
13	P-type delta doping in silicon MBE. <i>Thin Solid Films</i> , <b>1990</b> , 184, 15-19	2.2	28
12	Particulate contamination in silicon grown by molecular-beam epitaxy. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , <b>1990</b> , 8, 21		4
11	Photoluminescence properties of a-(Si/SiN):H multilayers: A comparison with bulk alloys. <i>Journal of Non-Crystalline Solids</i> , <b>1987</b> , 97-98, 883-886	3.9	3
10	Recombination in a-Si:H Based Materials: Evidence for Two Slow Radiative Processes <b>1987</b> , 357-368		17

9	A comparison of photo- and electroluminescence in a-Si p-i-n junctions. <i>Journal of Non-Crystalline Solids</i> , <b>1985</b> , 77-78, 695-698	3.9	10
8	Electrical, optical and luminescence properties of a-Si/SiN multilayers. <i>Journal of Non-Crystalline Solids</i> , <b>1985</b> , 77-78, 1081-1084	3.9	18
7	Low avalanche noise behaviour in bulk Al/sub 0.8/Ga/sub 0.2/As		2
6	Strain-balanced quantum wells for power FET applications		1
5	Vertical correlation-anticorrelation transition in InAs/GaAs quantum dot structures grown by molecular beam epitaxy251-254		
4	Effect of annealing on anticorrelated InGaAs/GaAs quantum dots255-258		
3	Structural analysis of the effects of a combined InAlAs-InGaAs capping layer in 1.3- $\mu\text{m}$ InAs quantum dots263-266		
2	Microstructural studies of InAs/GaAs self-assembled quantum dots grown by selective area molecular beam epitaxy267-270		
1	Activation energy for surface diffusion in GaInNAs quantum wells279-282		